

| | Document ID | Issue Date | Pages | Title |
|---|---------------|------------|-------|--|
| 1 | US 6549554 B2 | 20030415 | 19 | Semiconductor laser element, semiconductor etchant, and method of fabricating the semiconductor laser element |
| 2 | US 6545296 B1 | 20030408 | 10 | Semiconductor light emitting device |
| 3 | US 6472691 B2 | 20021029 | 13 | Distributed feedback semiconductor laser device |
| 4 | US 6472679 B1 | 20021029 | 60 | Semiconductor structures using a group III-nitride quaternary material system with reduced phase separation and method of fabrication |
| 5 | US 6377597 B1 | 20020423 | 22 | Gallium nitride semiconductor light emitting element with active layer having multiplex quantum well structure and semiconductor laser light source device |
| 6 | US 6232623 B1 | 20010515 | 14 | Semiconductor device on a sapphire substrate |
| 7 | US 5976904 A | 19991102 | 13 | Method of manufacturing semiconductor device |
| 8 | US 5960020 A | 19990928 | 16 | Semiconductor laser diode including ridge and partially disordered active layer |

| | Current OR |
|---|------------|
| 1 | 372/46 |
| 2 | 257/79 |
| 3 | 257/115 |
| 4 | 257/12 |
| 5 | 372/45 |
| 6 | 257/103 |
| 7 | 438/33 |
| 8 | 372/46 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|------|-----|------|---|---|---------------------|
| 1 | BRS | L1 | 1854 | laser and gaas and (ridge mesa) and electrode | USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2003/06/05 12:24 |
| 2 | BRS | L2 | 663 | 1 and 257/\$.ccls. | USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2003/06/05 12:25 |
| 3 | BRS | L35 | 145 | 438/39.ccls. and @ay<2001 | USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2003/06/05 13:43 |
| 4 | BRS | L36 | 493 | 438/40.ccls. and @ay<2001 | USPAT; EPO; JPO; DERWEN T; IBM_TD B | 2003/06/05 13:43 |

| | Document ID | Issue Date | Pages | Title |
|----|--------------|------------|-------|--|
| 9 | US 5939733 A | 19990817 | 12 | Compound semiconductor device having a group III-V compound semiconductor layer containing therein Tl and As |
| 10 | US 5892785 A | 19990406 | 13 | Semiconductor laser |
| 11 | US 5550393 A | 19960827 | 19 | Semiconductor layer structure having distributed strain and optical semiconductor device including such strained layer |
| 12 | US 5388117 A | 19950207 | 25 | Polarization insensitive semiconductor optical amplifier and an optical communication system using the same |
| 13 | US 5260588 A | 19931109 | 10 | Light-emitting diode array |
| 14 | US 4958202 A | 19900918 | 13 | Semiconductor light-emitting device and method of manufacturing the same |
| 15 | US 4719498 A | 19880112 | 17 | Optoelectronic integrated circuit |

| | Current OR |
|----|------------|
| 9 | 257/94 |
| 10 | 372/46 |
| 11 | 257/192 |
| 12 | 372/45 |
| 13 | 257/93 |
| 14 | 257/96 |
| 15 | 257/292 |

| | Document ID | Issue Date | Pages | Title |
|----|--------------|------------|-------|-------------------------------------|
| 16 | US 4142160 A | 19790227 | 13 | Hetero-structure injection laser |

| | |
|----|------------|
| | Current OR |
| 16 | 372/46 |